Silicon NPN Power Transistors 2SC2486

DESCRIPTION

·With TO-3PN package
·Complement to type 2SA1062
·High collector power dissipation

APPLICATIONS

·High power audio frequency amplifier

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

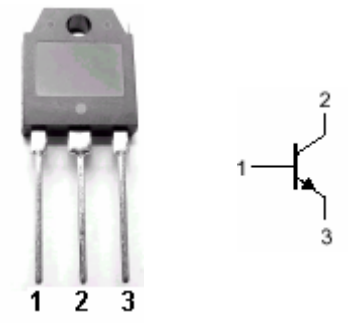


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	MAX	UNIT
V_{CBO}	Collector-base voltage	Open emitter	120	V
V_{CEO}	Collector-emitter voltage	Open base	120	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current (DC)		7	A
I_{CM}	Collector current-peak		12	A
P_C	Collector power dissipation	T_C=25□	80	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=25mA ;I_B=0	120			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=5A; I_B=0.5A			2.0	V
V_{BE}	Base-emitter on voltage	I_C=5A;V_{CE}=5V			1.8	V
I_{CBO}	Collector cut-off current	V_{CB}=120V; I_E=0			50	μA
I_{EBO}	Emitter cut-off current	V_{EB}=3V; I_C=0			50	μA
h_{FE-1}	DC current gain	I_C=0.02A ; V_{CE}=5V	20			
h_{FE-2}	DC current gain	I_C=1A ; V_{CE}=5V	40		200	
h_{FE-3}	DC current gain	I_C=5A ; V_{CE}=5V	20			
f_T	Transition frequency	I_C=0.5A ; V_{CE}=5V		20		MHz

◆ **h_{FE-2} Classifications**

R	Q	P
40-80	60-120	100-200

PACKAGE OUTLINE

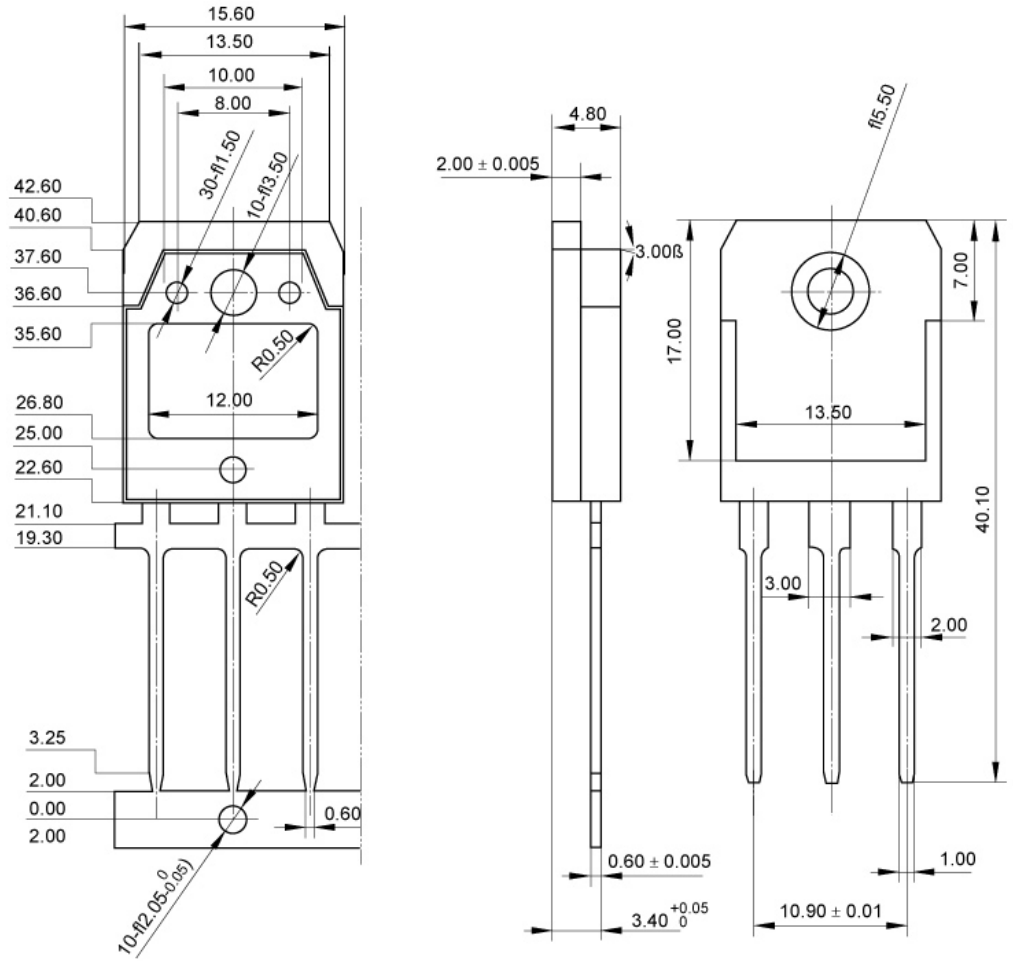


Fig.2 outline dimensions (unindicated tolerance:±0.1mm)